

# Tunability of optical absorption of MoS<sub>2</sub> by electrical gating and its application in a hybrid modulator

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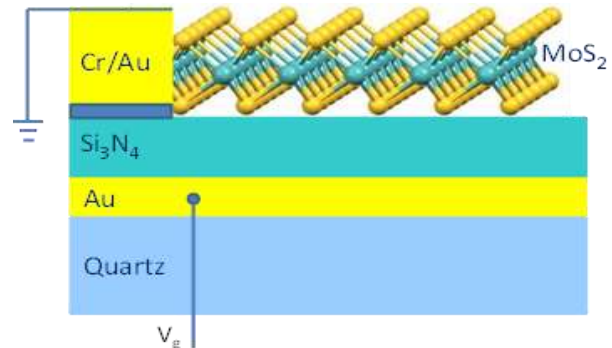
## Abstract

It was recently established that optical constants of 2D monolayers, in contrast to many bulk semiconducting materials such as Si, Ge, GaAs, could vary significantly with electrical field<sup>[1-2]</sup>. Here we investigated the electric field effect on optical properties of a monolayer of molybdenum disulphide (MoS<sub>2</sub>). This field effect is utilised to achieve ~10% visible light modulation for a hybrid electro-optical resonant modulator based on MoS<sub>2</sub>. A suggested hybrid nanostructure consists of a CMOS compatible Si<sub>3</sub>N<sub>4</sub> dielectric layer sandwiched between a thin gold film and a MoS<sub>2</sub> monolayer which enables a selective enhancement of polarised electro-absorption in a narrow window of angles of incidence and a narrow wavelength range near MoS<sub>2</sub> exciton transition energies. The possibility to modulate visible light with 2D materials and the robust nature of light modulation by MoS<sub>2</sub> could be useful for creation of reliable ultra-compact electro-optical hybrid visible-light modulators.

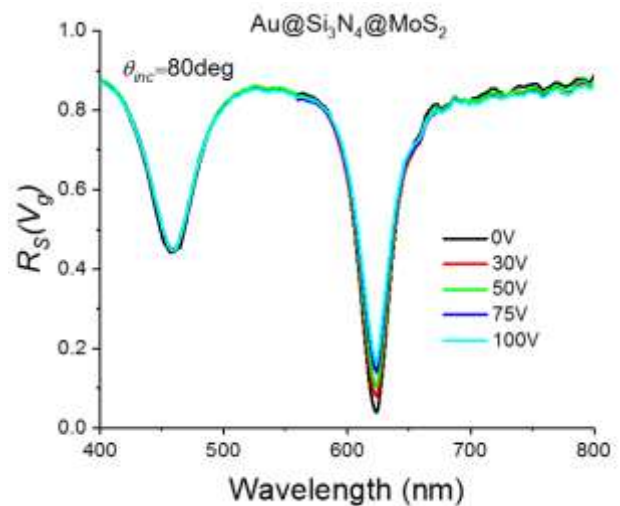
## References

- [1] Reed, G. T.; Mashanovich, G.; Gardes, F.Y.; Thomson, D.J., *Nat. Photon*, 4(2017), 518-526.
- [2] Mak, K.; Shan, J., *Nat. Photon*, 10 (2016) 216-226.

## Figures



**Figure 1:** Schematic illustration of the Au/Si<sub>3</sub>N<sub>4</sub>/MoS<sub>2</sub> modulator structure.



**Figure 2:** Change in s-polarised reflectance in the Au/Si<sub>3</sub>N<sub>4</sub>/MoS<sub>2</sub> hybrid modulator for different gating voltages with an incident angle of 80 degree.